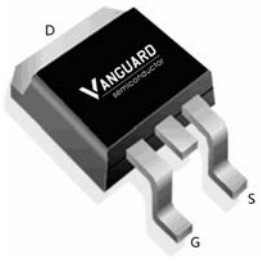
V_{DS}	60	V
$R_{DS(on),TYP}$@ V_{GS}=10 V	8.5	mΩ
I_D	55	A

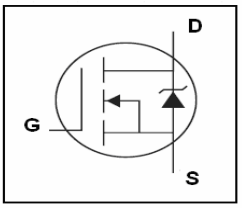
Features

- N-Channel，Logic Level 10V
- Enhancement mode
- Very low on-resistance
- Fast Switching
- 100% Avalanche Tested
- Pb-free lead plating; RoHS compliant

TO-263



Part ID	Package Type	Marking	Tape and reel information
VST012N06HS	TO-263	012N06H	800pcs/Reel



Maximum ratings, at T_j=25 °C, unless otherwise specified

Symbol	Parameter		Rating	Unit
$V_{(BR)DSS}$	Drain-Source breakdown voltage		60	V
I_S	Diode continuous forward current	T_C=25°C	55	A
I_D	Continuous drain current@V_{GS}=10V	T_C=25°C	55	A
		T_A=100°C	35	A
I_{DM}	Pulse drain current tested ①	T_C=25°C	200	A
EAS	Avalanche energy, single pulsed ②	L=0.1mH	156	mJ
IAS	Avalanche Current, single pulsed ②		56	A
P_D	Maximum power dissipation	T_A=25°C	86	W
V_{GS}	Gate-Source voltage		±20	V
T_{STG} T_J	Storage and operating temperature range		-55 to 175	°C

Thermal Characteristics

Symbol	Parameter	Typical	Unit
$R_{\theta JC}$	Thermal Resistance-Junction to Case	1.3	°C/W
$R_{\theta JA}$	Thermal Resistance Junction-Ambient	50	°C/W

Typical Characteristics

Symbol	Parameter	Condition	Min.	Typ.	Max.	Unit
Static Electrical Characteristics @ T_C = 25°C (unless otherwise stated)						
$V_{(BR)DSS}$	Drain-Source Breakdown Voltage	V_{GS}=0V I_D=250μA	60	--	--	V
I_{DSS}	Zero Gate Voltage Drain Current(Tc=25℃)	V_{DS}=60V,V_{GS}=0V	--	--	1	μA
	Zero Gate Voltage Drain Current(Tc=125℃)	V_{DS}=60V,V_{GS}=0V	--	--	100	μA
I_{GSS}	Gate-Body Leakage Current	V_{GS}=±20V,V_{DS}=0V	--	--	±100	nA
$V_{GS(TH)}$	Gate Threshold Voltage	V_{DS}=V_{GS},I_D=250μA	2.0	2.5	3.5	V
$R_{DS(ON)}$	Drain-Source On-State Resistance③	V_{GS}=10V, I_D=40A	--	8.5	12	mΩ
$R_{DS(ON)}$	Drain-Source On-State Resistance③	V_{GS}=6V, I_D=20A	--	11	16	mΩ
Dynamic Electrical Characteristics @ T_C= 25°C (unless otherwise stated)						
C_{iss}	Input Capacitance	V_{DS}=24V,V_{GS}=0V, f=1MHz	--	1860	--	pF
C_{oss}	Output Capacitance		--	150	--	pF
C_{rss}	Reverse Transfer Capacitance		--	95	--	pF
Q_g	Total Gate Charge	V_{DS}=30V,I_D=10A, V_{GS}=10V	--	26	--	nC
Q_{gs}	Gate-Source Charge		--	6.5	--	nC
Q_{gd}	Gate-Drain Charge		--	4.5	--	nC
Switching Characteristics						
$t_{d(on)}$	Turn-on Delay Time	V_{DD}=30V, I_D=10A, R_G=6.8Ω, V_{GS}=10V	--	9	--	nS
t_r	Turn-on Rise Time		--	5	--	nS
$t_{d(off)}$	Turn-Off Delay Time		--	28	--	nS
t_f	Turn-Off Fall Time		--	4	--	nS
Source- Drain Diode Characteristics@ T_C = 25°C (unless otherwise stated)						
V_{SD}	Forward on voltage	I_{SD}=40A,V_{GS}=0V	--	0.91	1.2	V
t_{rr}	Reverse Recovery Time	T_j=25℃,I_{sd}=20A, V_{GS}=0V di/dt=100A/μs	--	23	--	nS
Q_{rr}	Reverse Recovery Charge			52		nC

NOTE:

① Repetitive rating; pulse width limited by max. junction temperature.

② Limited by T_{Jmax}, starting T_J = 25°C, L = 0.1mH,R_G = 25Ω, I_{AS} = 56A, V_{GS} =10V. Part not recommended for use above this value

③ Pulse width ≤ 300μs; duty cycle≤ 2%.

Typical Characteristics

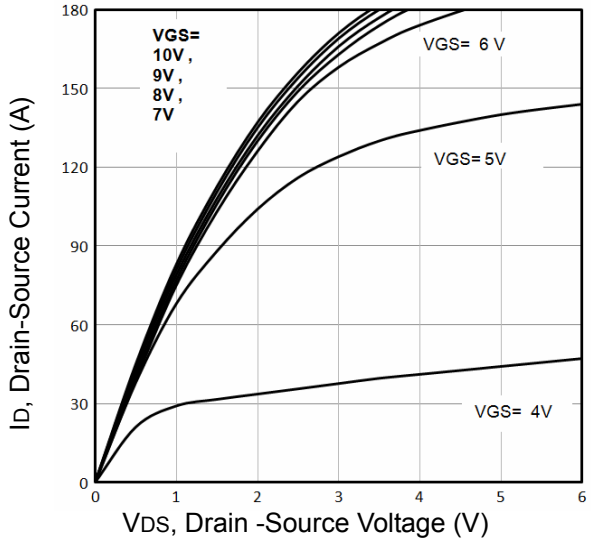


Fig1. Typical Output Characteristics

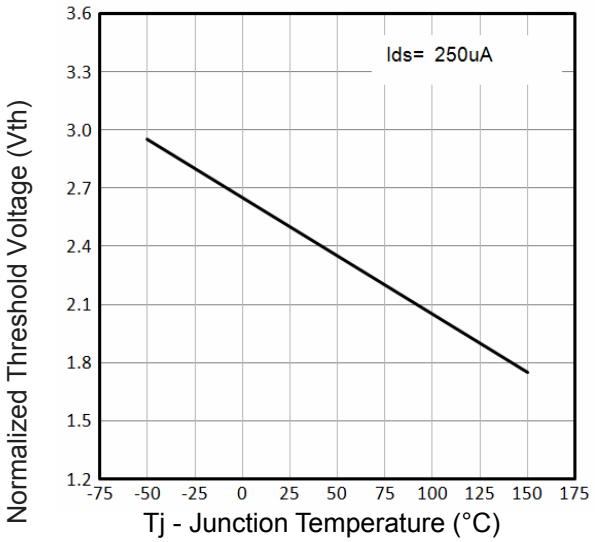


Fig2. Normalized Threshold Voltage Vs. Temperature

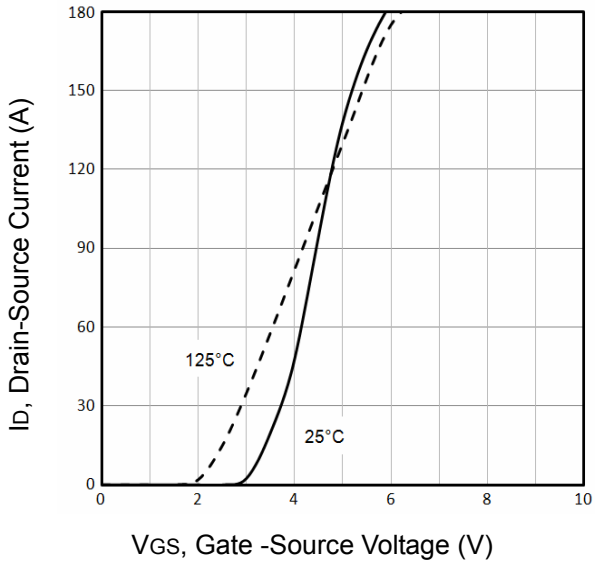


Fig3. Typical Transfer Characteristics

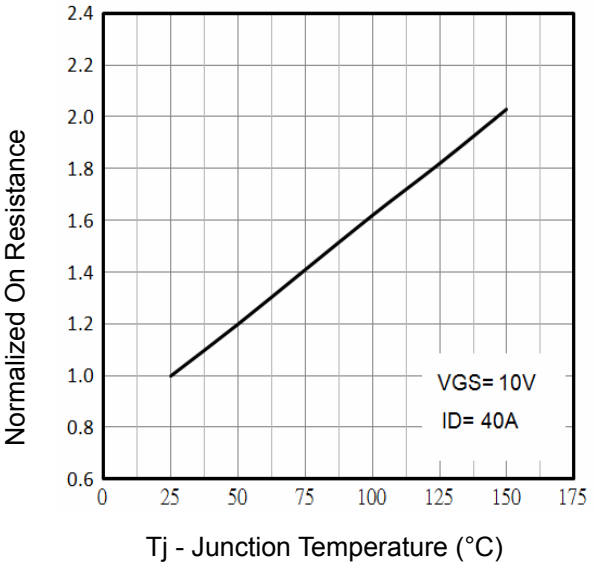


Fig4. Normalized On-Resistance Vs. Temperature

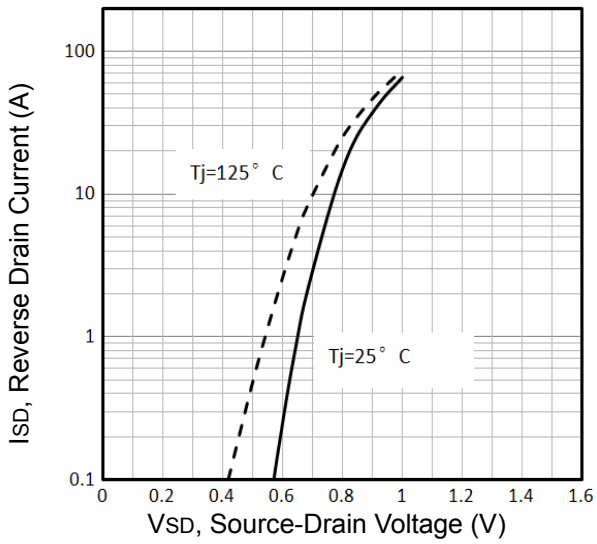


Fig5. Typical Source-Drain Diode Forward Voltage

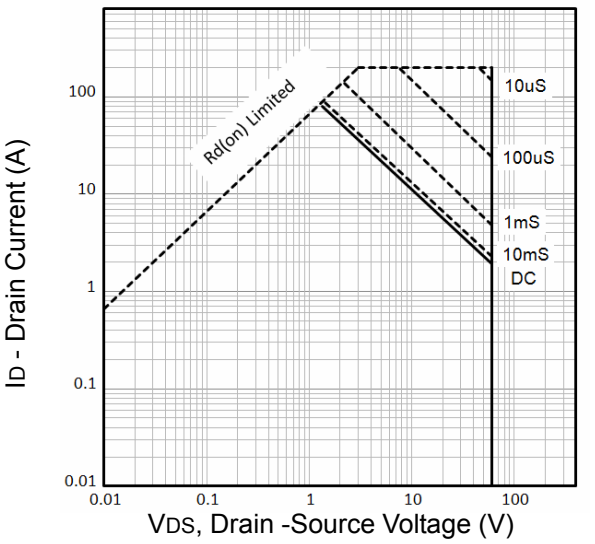


Fig6. Maximum Safe Operating Area

Typical Characteristics

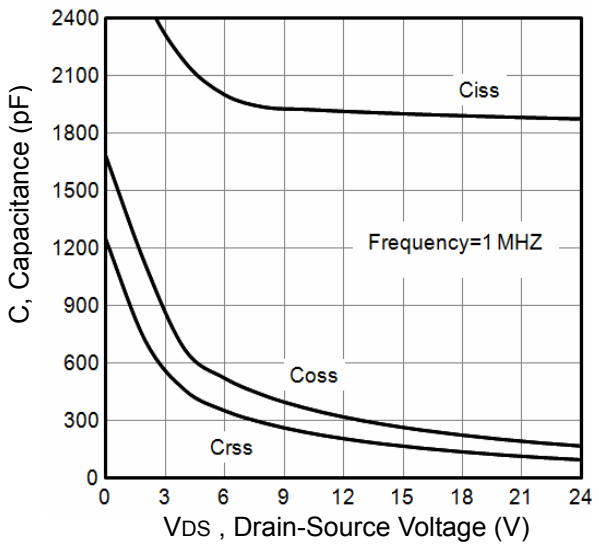


Fig7. Typical Capacitance Vs.Drain-Source Voltage

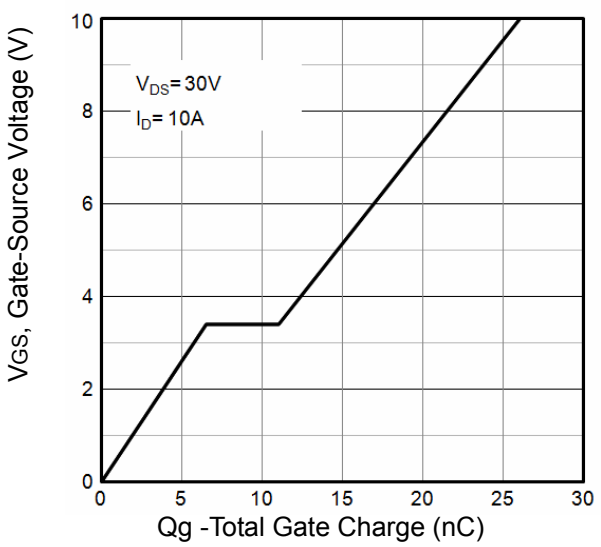


Fig8. Typical Gate Charge Vs.Gate-Source

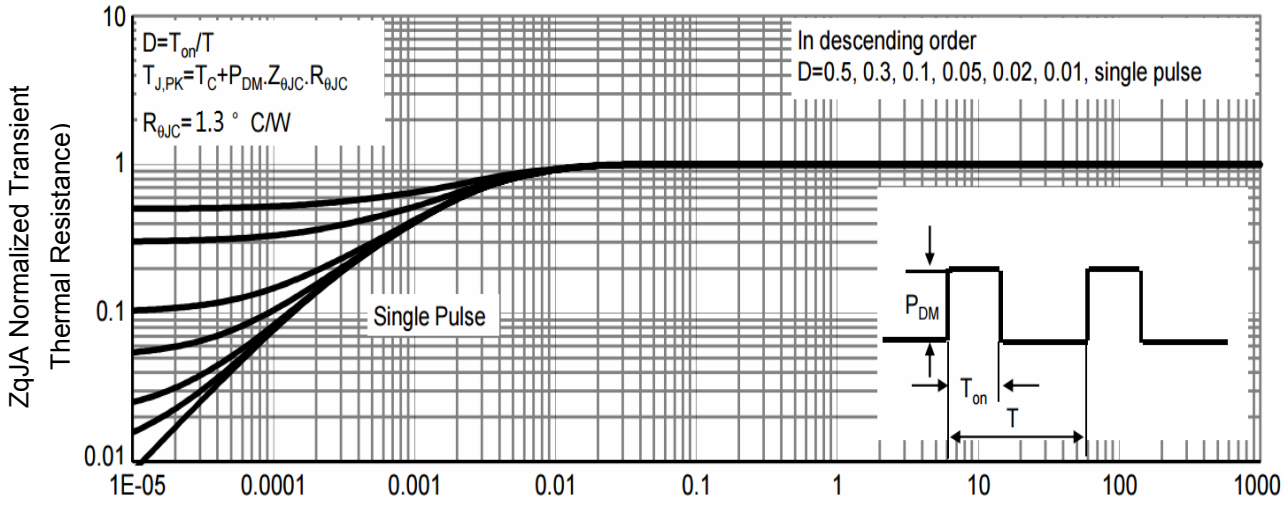


Fig9. Normalized Maximum Transient Thermal Impedance

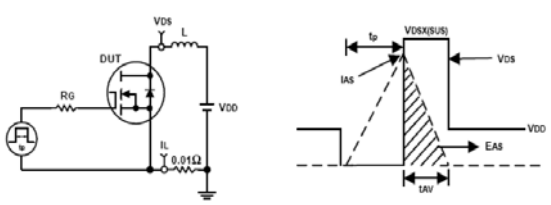


Fig10. Unclamped Inductive Test Circuit and waveforms

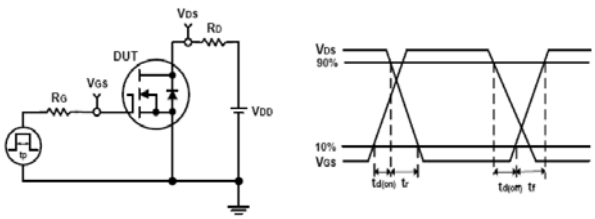
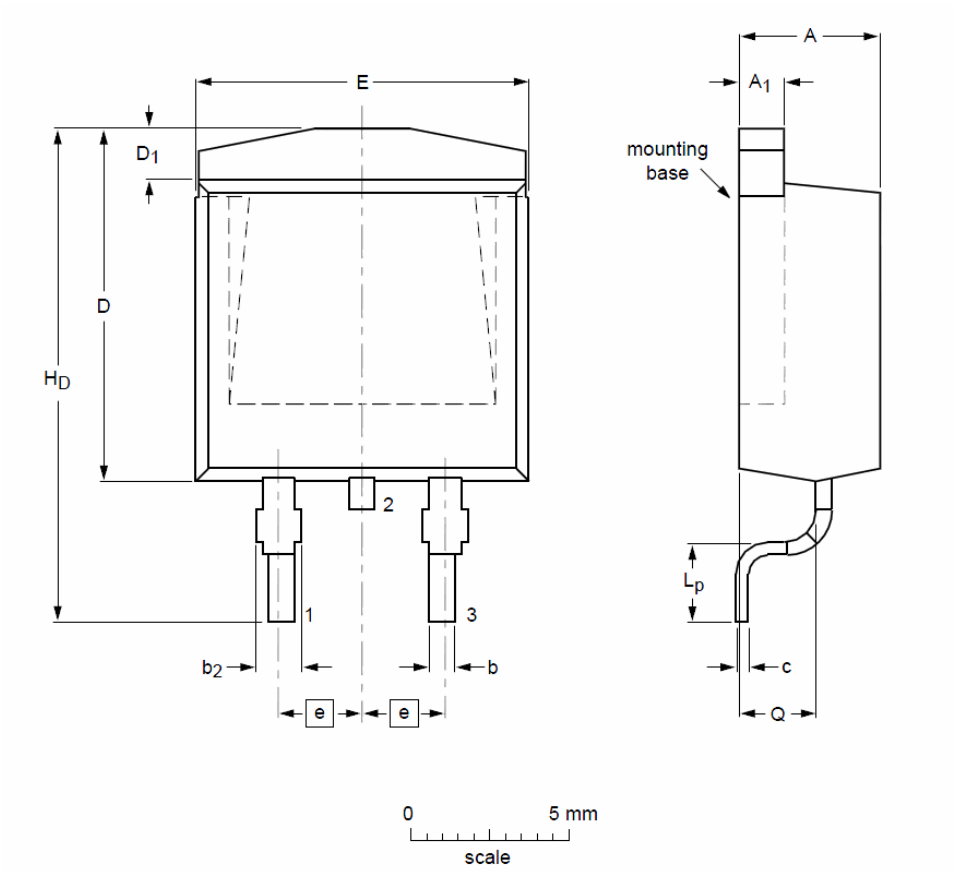


Fig11. Switching Time Test Circuit and waveforms

TO-263 Package Outline Data



DIMENSIONS (unit : mm)

Symbol	Min	Typ	Max	Symbol	Min	Typ	Max
A	4.10	4.40	4.50	**A_1**	1.27	1.32	1.40
b	0.60	0.76	0.85	**b_2**	1.05	1.30	1.45
c	0.46	0.54	0.64	**D**	10.20	10.40	11.00
D_1	1.20	1.51	1.60	**E**	9.70	10.10	10.30
e	--	2.54	--	**H_D**	14.80	15.45	15.80
L_P	2.10	2.40	2.90	**Q**	2.20	2.50	2.60

Customer Service

Sales and Service:
sales@vgsemi.com
Vanguard Semiconductor CO., LTD
TEL: (86-755) -26902410
FAX: (86-755) -26907027
WEB: **www.vgsemi.com**